

GaTe



VITAL
Grade: 6N/6.5N

Properties: Gallium telluride (GaTe) is synthesized by high purity gallium and high purity tellurium proportionally in high temperature. It is gray-black, brittle, with a certain degree of laxity.

Uses: It is used in preparing solar cells, photovoltaic devices, semiconductor device manufacturing and MBE (molecular beam epitaxy) material.

· Identifier

Chemical Formula	GaTe
CAS No.	12024-14-5
EINECS No.	234-690-1

· Physical and chemical properties

Molecular weight	197.32 g/mol	Flash point	/	Reactivity	Easily oxidized in air
Appearance	Gray-black solid	Melting point	790℃	Solubility	Reacts with acids and alkalis
Density	5.57 g/cm ³	Boiling point	/	Storage	Shady and cool, well-ventilated

· Metal impurities

Impurities	6N/ppbw	6.5N/ppbw	Impurities	6N/ppbw	6.5N/ppbw
Na	≤100	≤100	Ge	≤50	≤50
Mg	≤10	≤10	As	≤20	≤20
Al	≤20	≤20	Se	≤50	≤50
Si	≤200	≤100	Mo	≤10	≤10
K	≤50	≤20	Ag	≤100	≤100
Ca	≤200	≤100	Cd	≤50	≤10
Ti	≤10	≤10	In	≤100	≤100
V	≤10	≤10	Sn	≤20	≤20
Cr	≤20	≤20	Sb	≤20	≤20
Mn	≤20	≤20	Hg	≤20	≤20
Fe	≤20	≤20	Tl	≤10	≤10
Ni	≤20	≤20	Pb	≤20	≤20
Co	≤10	≤10	Bi	≤10	≤10
Cu	≤20	≤20	Combined total impurities	≤1000	≤500
Zn	≤100	≤100			

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